

Supplementary Material for “Interfacial Charge Transfer Induced Electronic Property Tuning of MoS₂ by Molecular Functionalization”

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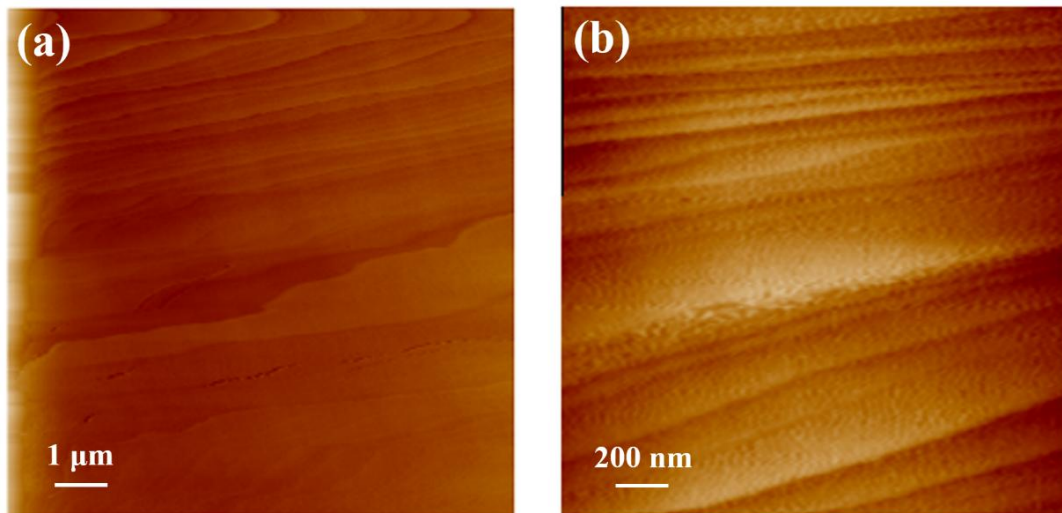


Figure S1 AFM images (10 $\mu\text{m} \times 10 \mu\text{m}$) and (2 $\mu\text{m} \times 2 \mu\text{m}$) of bulk MoS₂.

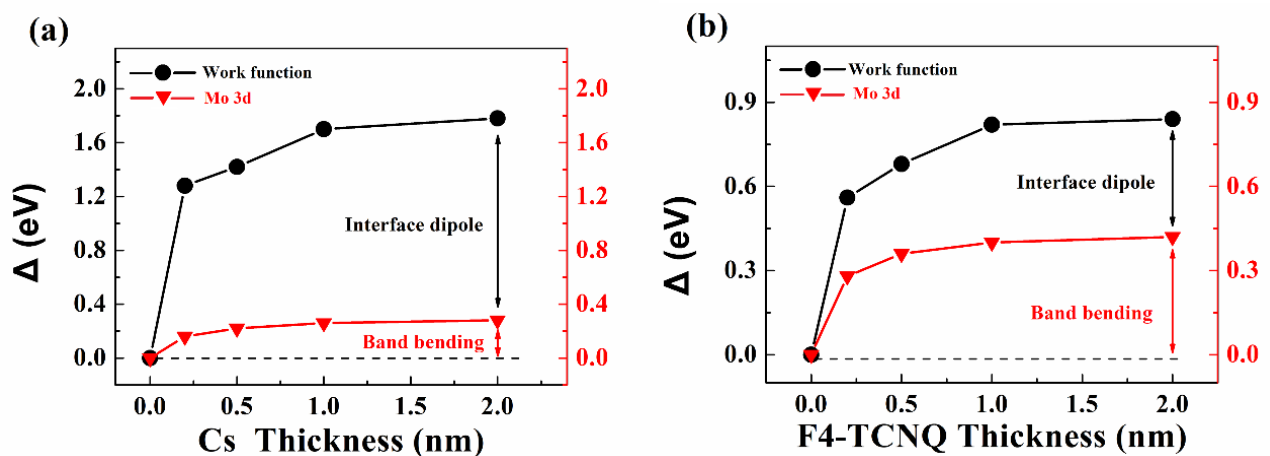


Figure S2 The plot of the sample work function and Mo 3d of MoS₂ as a function of the (a) Cs and (b) F4-TCNQ coverage.

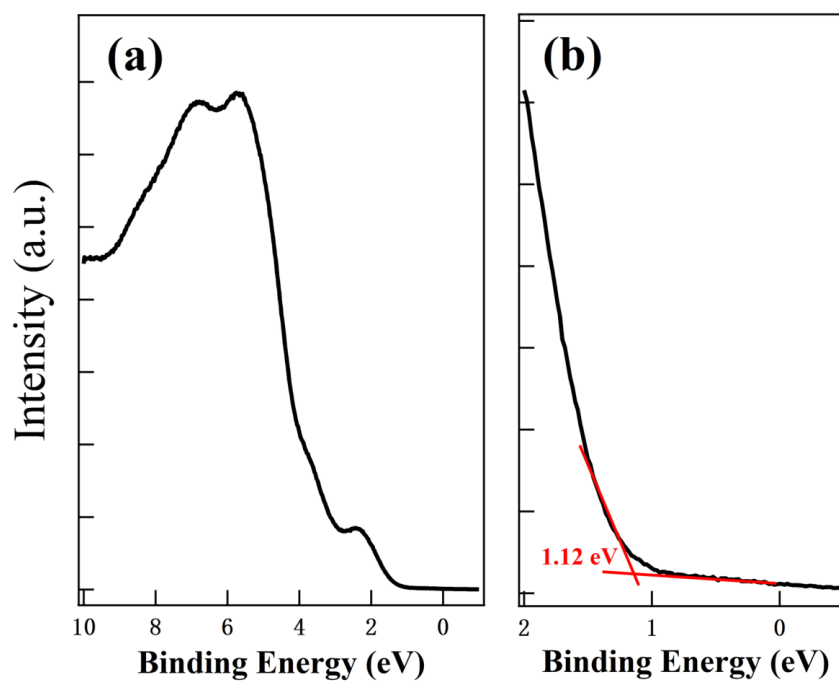


Figure S3 UPS spectrum of bulk MoS₂ at (a) the low binding energy part and (b) near the EF region.